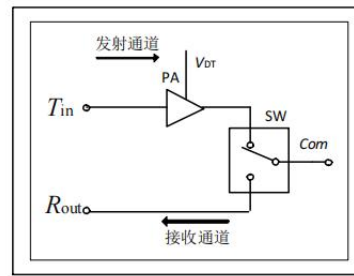


Performance

- Frequency: 32~40GHz
- Typical Signal Gain: 21dB
- Typical Pout: 31dBm@18V
- Typical PAE: 22.5%
- Bias: 18V, -1.8V (Typ.)
- Technology: 0.15um HEMT
- Size: 3.8*2.2mm*0.05mm

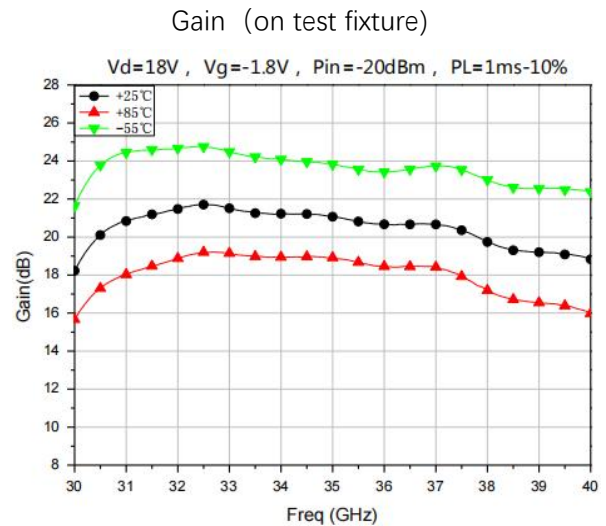
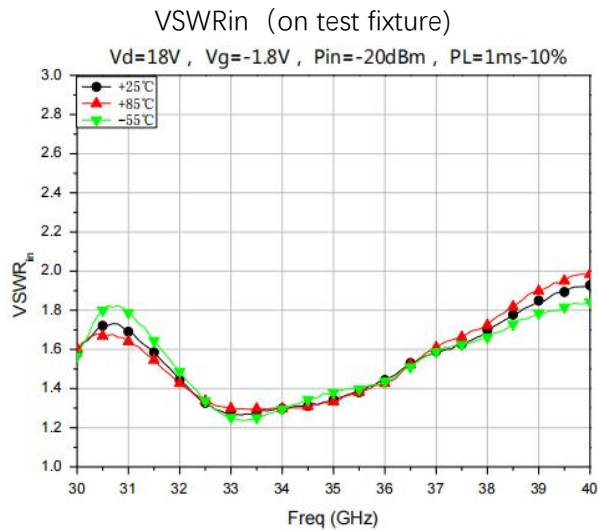
Function Diagram



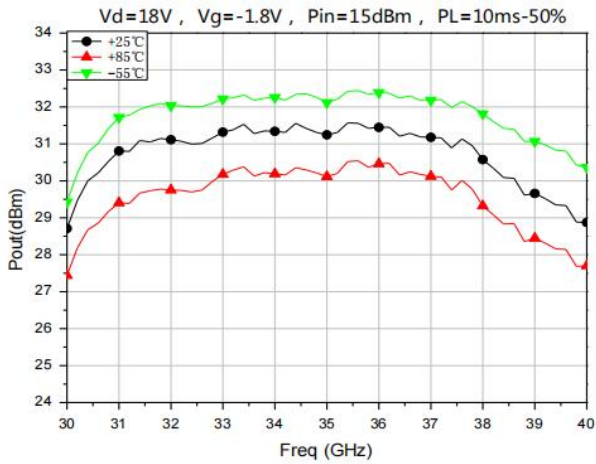
Electrical Specifications (T_A=25°C, V_d=18V, V_g=-1.8V, V₁/V₂=-28V/0V, F: 32~40GHz, D.C=50%)

Symbol	Parameter	Min	Typical	Max	Unit
G	Small Signal Gain	-	21	-	dB
G _p	Power Gain	-	16.5	-	dB
P _{out}	Saturated Power	-	31	-	dBm
I _d	Dynamic Current	-	265	-	mA
PAE	Power Added Efficiency	-	22.5	-	%

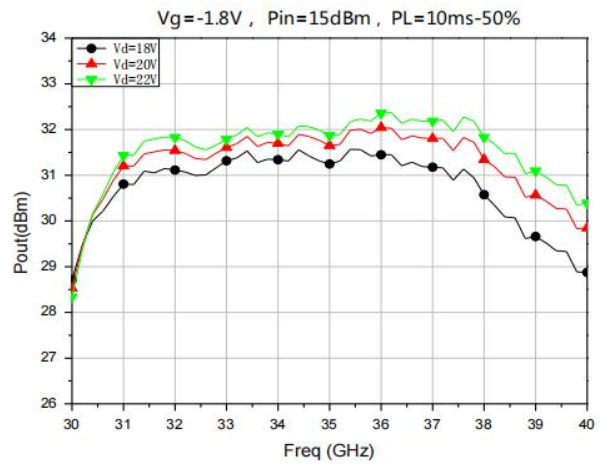
Test Curves



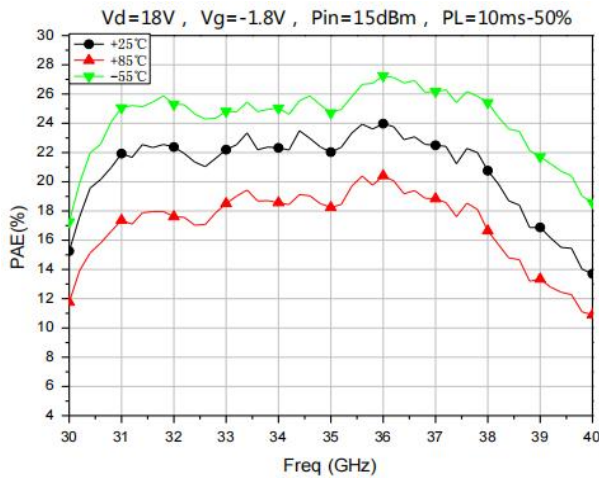
Pout 1 (on test fixture)



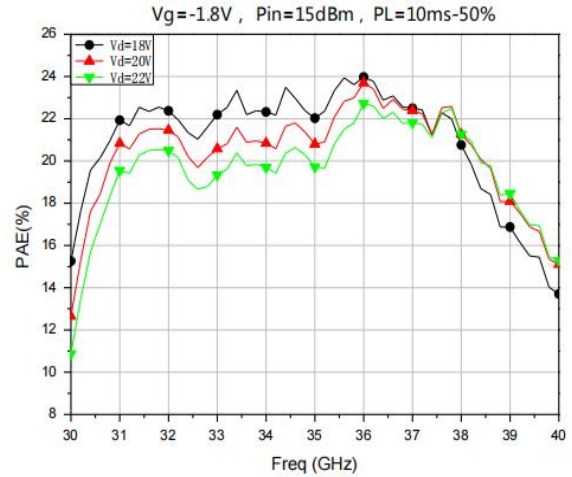
Pout 2 (on test fixture)



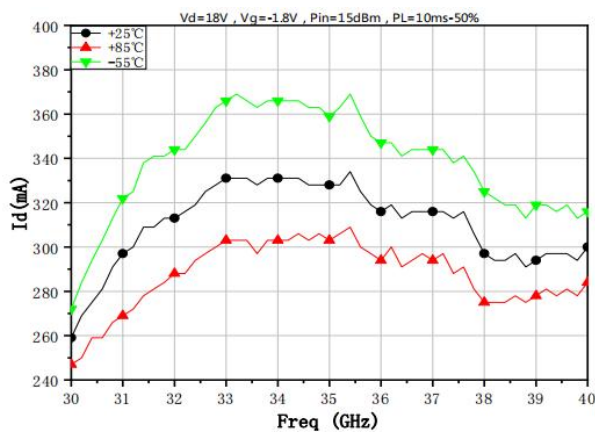
PAE 1 (on test fixture)



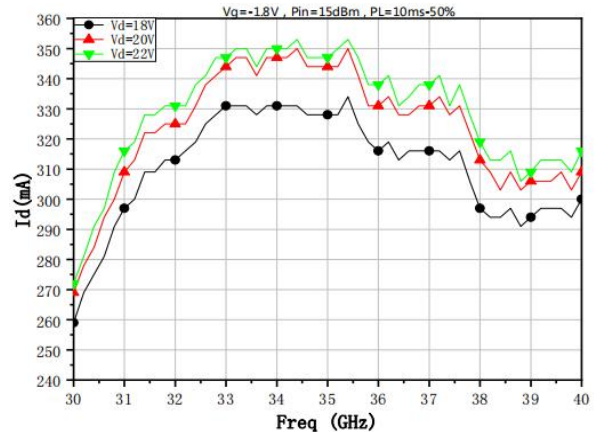
PAE 2 (on test fixture)



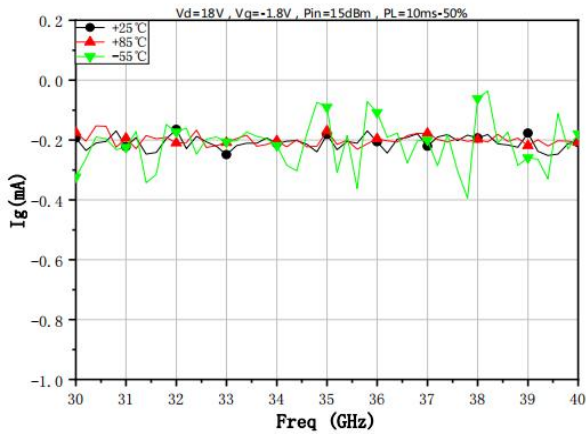
ID 1 (on test fixture)



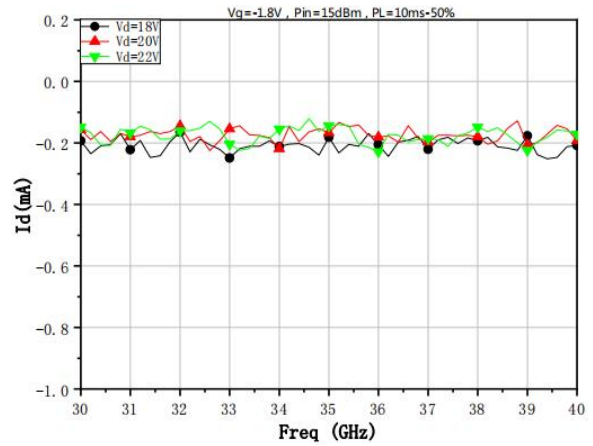
ID 2 (on test fixture)



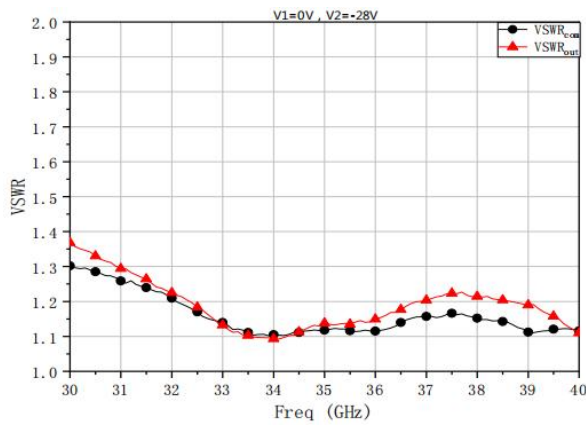
Ig 1 (on test fixture)



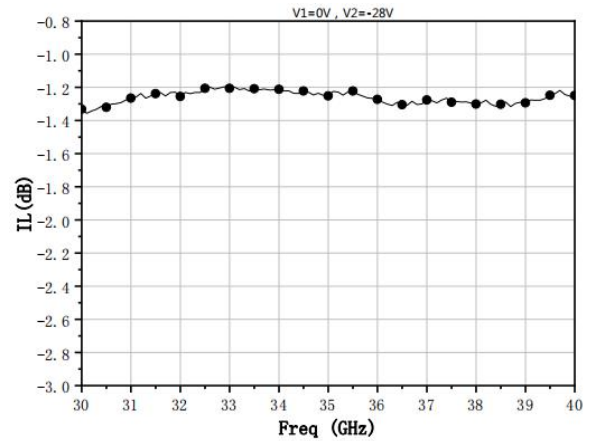
Ig 2 (on test fixture)



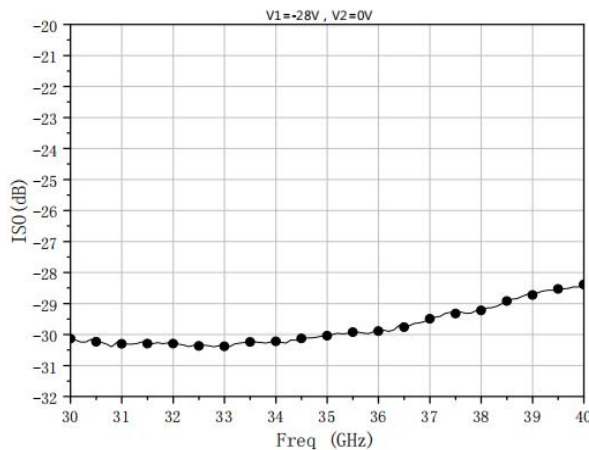
VSWR (on wafer)



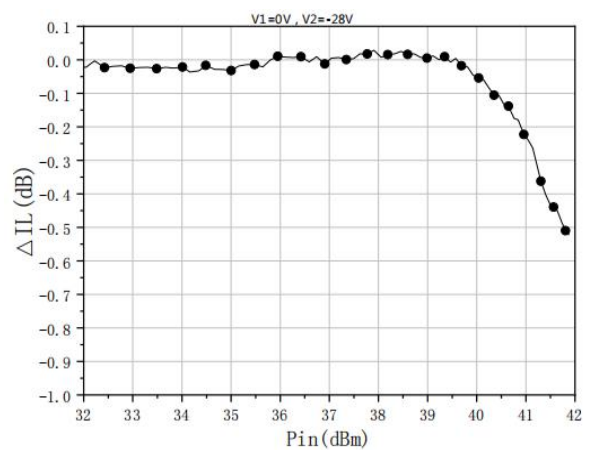
IL (on wafer)



ISO (on wafer)



ΔIL (on wafer)



Truth Table

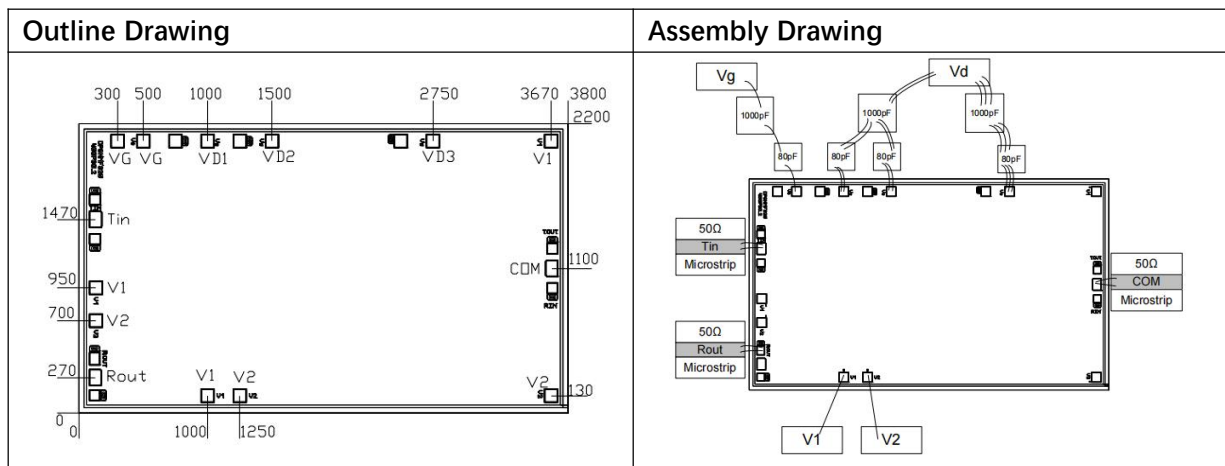
V1	V2	Tin-COM	COM-Rout
0	1	TURN-ON	TURN-OFF
1	0	TURN-OFF	TURN-ON

Note: "0" is low level -30V~-28V, "1" is high level 0V~0.5V.


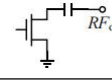
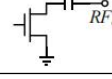
Absolute Max Ratings (TA=25°C)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	28V	
Id	Drain Current	0.6A	
Vg	Gate Voltage	-10V	
Ig	Gate Current	10mA	
Pd	DC Power	16W	
Pin	Input Power	20dBm	
Tch	Channel Temperature	225°C	
Tm	Mounting Temperature	290°C	1 min, N2 Protection
Tstg	Storage Temperature	-65~150°C	

Exceeding any one or combination of these limits may cause permanent damage.



Pads Definition

Pad	Description	Equivalent Circuit
Tin	RF Signal input, connect to 50ohm system, no need block capacitor.	
RFout	RF Signal output, connect to 50ohm system, no need block capacitor.	
COM	RF Signal transmitting output/receiving input, connect to 50ohm system, no need block capacitor.	
VG	Amp gate bias, external 80pF, 1000pF capacitor is needed	